

IN THE CLAIMS:

Please amend the claims as follows:

Sub 1  
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8. (Amended) An ohmic contact in a semiconductor device which is formed on a semiconductor material, the ohmic contact comprising a mixture of p-type semiconductor oxide and metal.

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9. (Amended) The ohmic contact as claimed in claim 8 wherein the p-type semiconductor oxide includes a single oxide.

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10. (Amended) The ohmic contact as claimed in claim 8 wherein the p-type semiconductor oxide includes a mixture of various oxides.

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11. (Amended) The ohmic contact as claimed in claim 8 wherein the p-type semiconductor oxide includes a solid solution of various oxides.

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12. (Amended) The ohmic contact as claimed in claim 8 wherein the semiconductor material is p-type  $\text{Al}_x\text{Ga}_y\text{In}_z\text{N}$ , and  $0 < x, y, z < 1$ , and  $x + y + z = 1$ .

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13. (Amended) The ohmic contact as claimed in claim 8 wherein the p-type semiconductor oxide is one of  $\text{NiO}$ ,  $\text{MnO}$ ,  $\text{FeO}$ ,  $\text{Fe}_2\text{O}_3$ ,  $\text{CoO}$ ,  $\text{CrO}$ ,  $\text{Cr}_2\text{O}_3$ ,  $\text{CrO}_2$ ,  $\text{CuO}$ ,  $\text{Cu}_2\text{O}$ ,  $\text{SnO}$ ,  $\text{Ag}_2\text{O}$ ,  $\text{CuAlO}_2$ ,  $\text{SrCu}_2\text{O}_2$  and  $\text{PdO}$ .

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14. (Amended) The ohmic contact as claimed in claim 8 wherein the metal is Au, Pt, Rh, Ru, or Ir.

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15. (Amended) The ohmic contact as claimed in claim 12 wherein the semiconductor material is p-type  $\text{GaN}$ .

Sub 1  
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16. (Amended) An ohmic contact in a semiconductor device, which is formed on a semiconductor material, the ohmic contact comprising a layer of p-type semiconductor oxide and a conductive layer.

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17. (Amended) The ohmic contact as claimed in claim 16 wherein the semiconductor material is p-type  $\text{Al}_x\text{Ga}_y\text{In}_z\text{N}$ , and  $0 < x, y, z < 1$ , and  $x + y + z = 1$ .

1                   18.     (Amended) The ohmic contact as claimed in claim 16 wherein the p-type  
2 semiconductor oxide is one of NiO, MnO, FeO, Fe<sub>2</sub>O<sub>3</sub>, CoO, CrO, Cr<sub>2</sub>O<sub>3</sub>, CrO<sub>2</sub>, CuO, Cu<sub>2</sub>O,  
3 SnO, Ag<sub>2</sub>O, CuAlO<sub>2</sub>, SrCu<sub>2</sub>O<sub>2</sub>, LaMnO<sub>3</sub>, YBa<sub>2</sub>Cu<sub>4</sub>O<sub>8</sub> and PdO.

1                   19.     (Amended) The ohmic contact as claimed in claim 16 wherein the layer of  
2 semiconductor oxide includes a single oxide layer.

1                   20.     (Amended) The ohmic contact as claimed in claim 16 wherein the layer of  
2 semiconductor oxide includes a plurality of layers of oxides of the same conductivity type.

1                   21.     (Amended) The ohmic contact as claimed in claim 16 wherein the layer of  
2 semiconductor oxide includes a mixture layer of various oxides.

1                   22.     (Amended) The ohmic contact as claimed in claim 16 wherein the layer of  
2 semiconductor oxide includes a solid solution layer consisting of various oxides.

1                   23.     (Amended) The ohmic contact as claimed in claim 16 wherein the  
2 conductive layer includes a single metal layer.

1                   24.     (Amended) The ohmic contact as claimed in claim 16 wherein the  
2 conductive layer includes a plurality of metal layers.

1                   25.     (Amended) The ohmic contact as claimed in claim 16 wherein the  
2 conductive layer is a transparent conductive film.

1                   26.     (Amended) The ohmic contact as claimed in claim 17 wherein the  
2 semiconductor material is p-type GaN.

1                   27.     (Amended) The ohmic contact as claimed in claim 25 wherein the  
2 transparent conductive film is conductive oxide, including indium-tin oxide, ZnO and ZnO doped  
3 with Ga, In, Al or Ce.

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Concl'd